



SANYO Semiconductors

## DATA SHEET

# 2SA2207

 — PNP Epitaxial Planar Silicon Transistor  
**50V / 13A High-Speed Switching Applications**

## Applications

- High-speed switching applications (switching regulators, drive circuit).

## Features

- Adoption of MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.

## Specifications

### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		-50	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		-50	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		-6	V
Collector Current	I <sub>C</sub>		-13	A
Collector Current (Pulse)	I <sub>CP</sub>		-15	A
Base Current	I <sub>B</sub>		-2	A
Collector Dissipation	P <sub>C</sub>		1	W
		T <sub>C</sub> =25°C	20	W
Junction Temperature	T <sub>J</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0A			-10	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0A			-10	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-270mA	200		500	
	h <sub>FE2</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-8.1A	50			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-700mA		110		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz		100		pF

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# 2SA2207

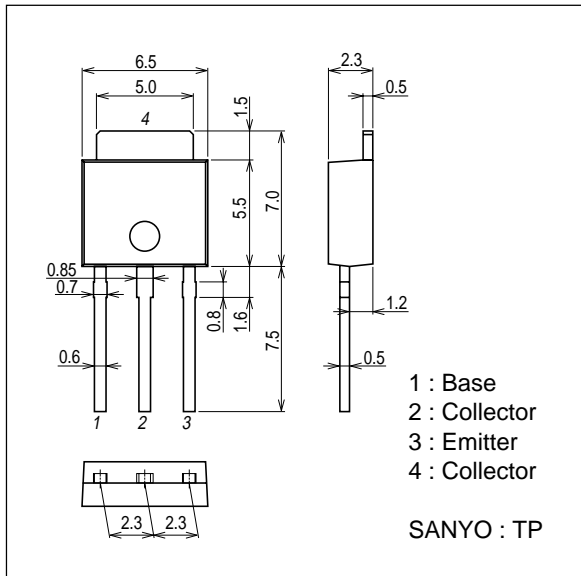
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -6A, I_B = -300mA$		-250	-500	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -6A, I_B = -300mA$			-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0A$	-50			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0A$	-6			V
Turn-ON Time	$t_{on}$	See specified Test Circuit.		80		ns
Storage Time	$t_{stg}$	See specified Test Circuit.		265		ns
Fall Time	$t_f$	See specified Test Circuit.		43		ns

## Package Dimensions

unit : mm (typ)

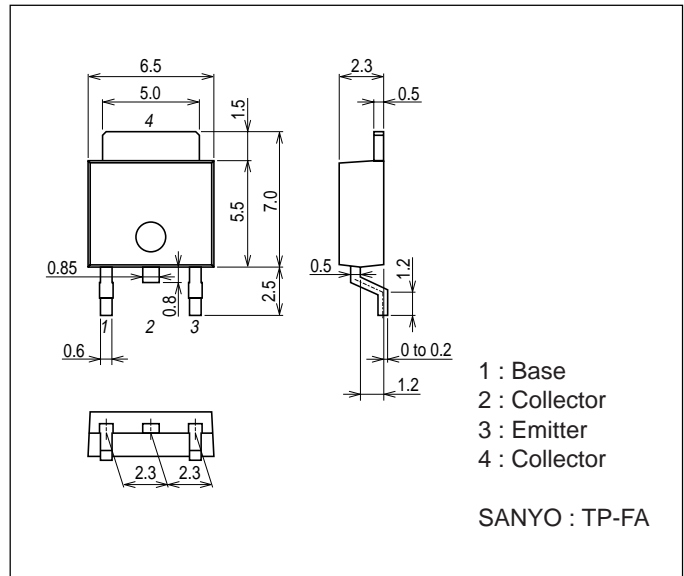
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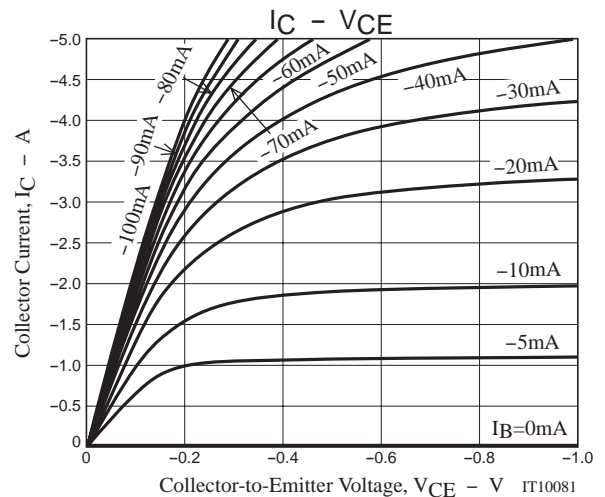
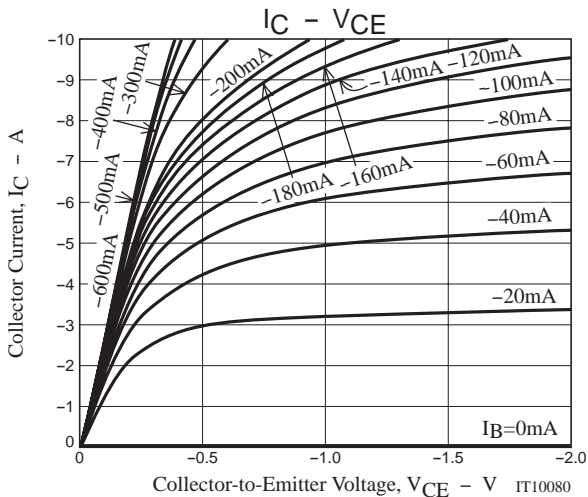
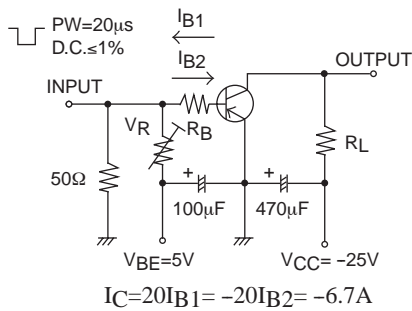
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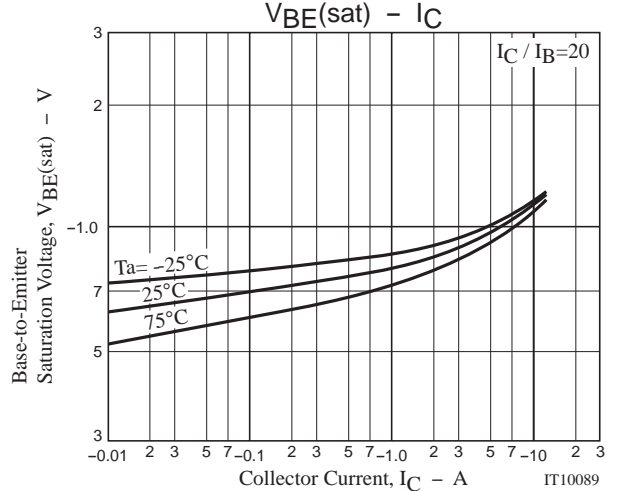
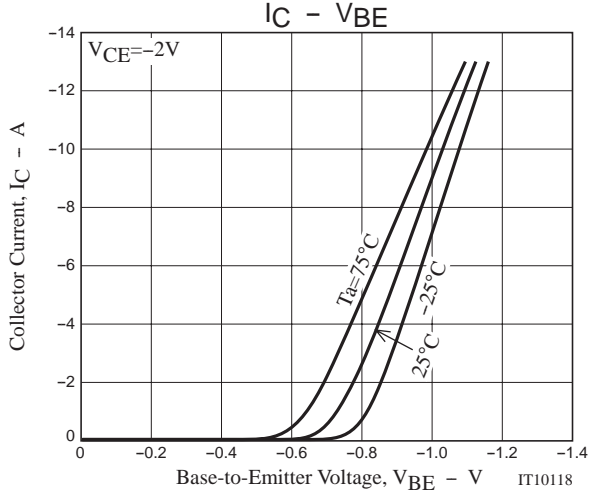
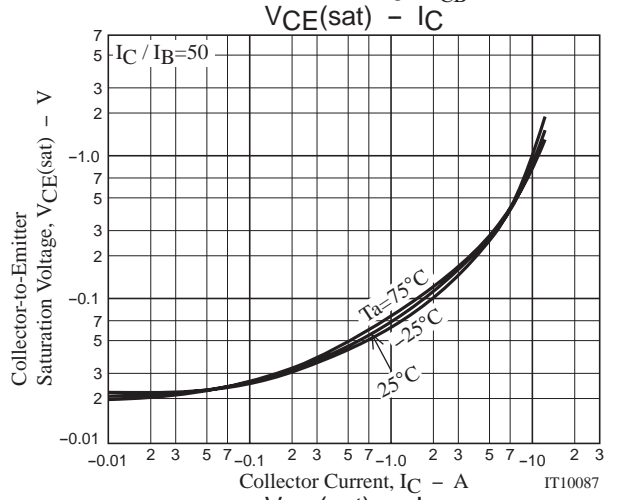
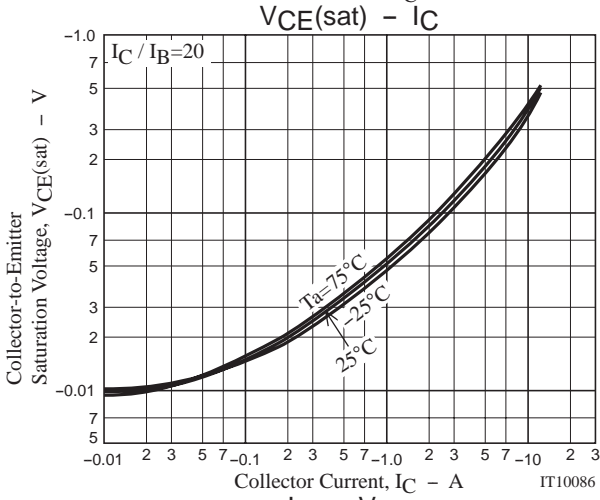
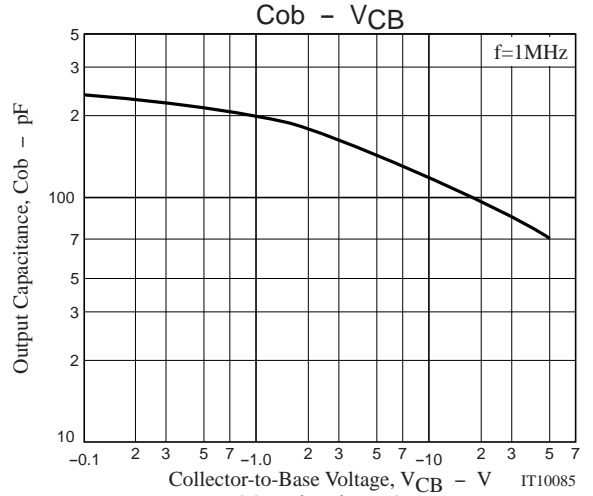
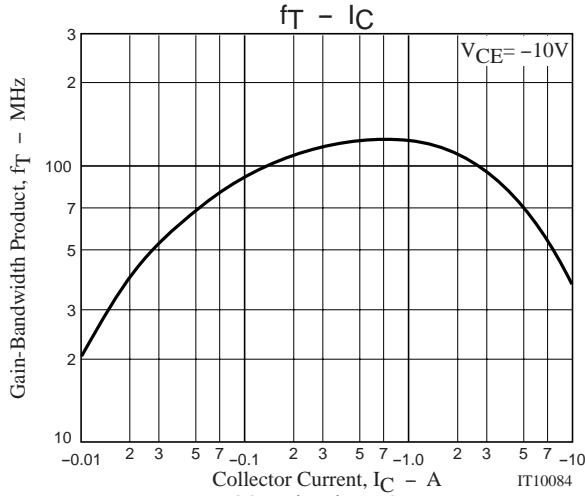
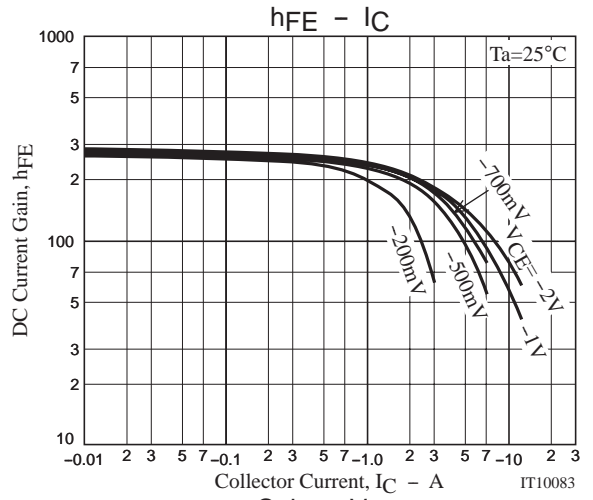
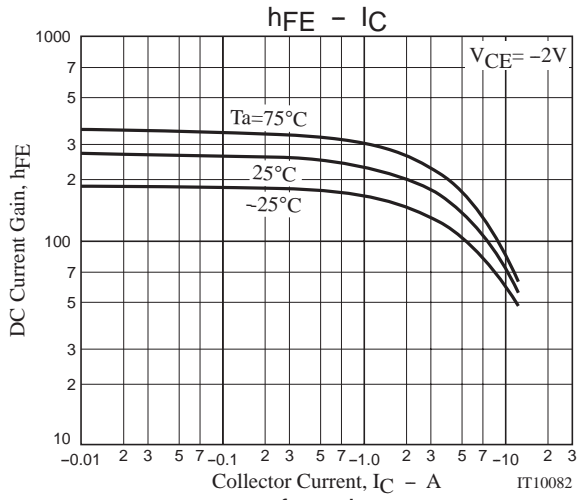
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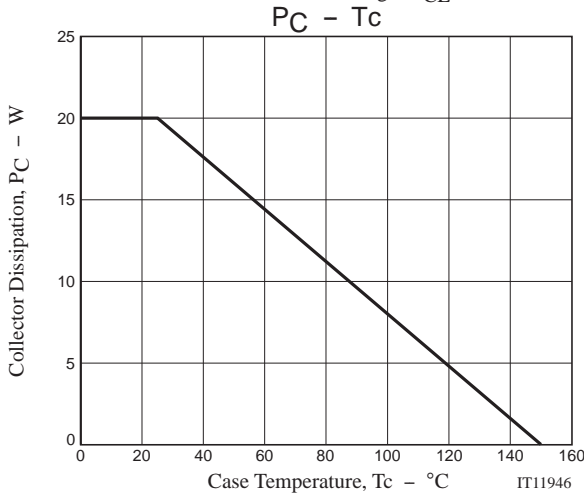
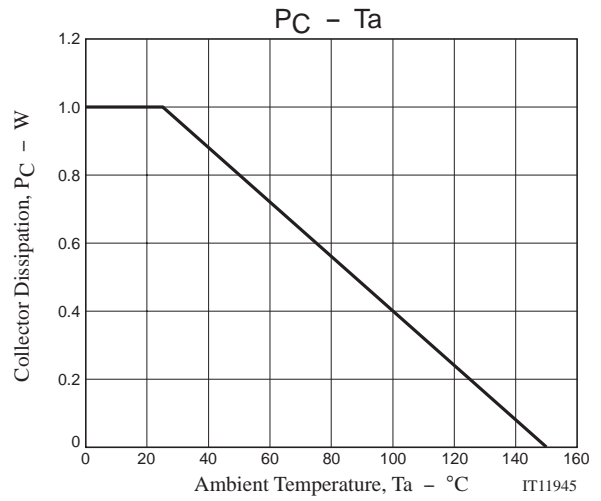
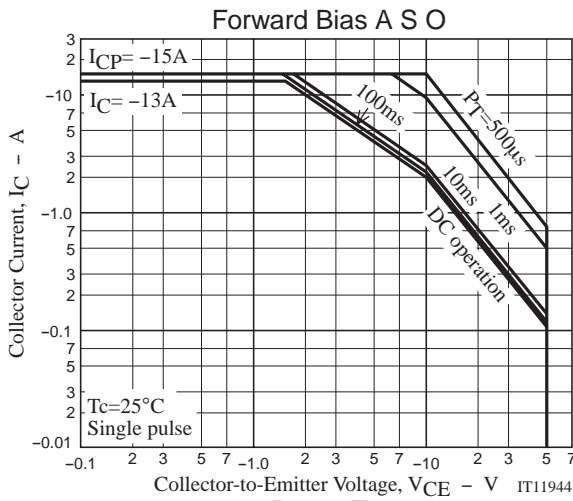
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## Switching Time Test Circuit







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